

L Number	Hits	Search Text	DB	Time stamp
12	4409	(silicon near oxide/silicon near nitride/silicon near oxide) (ONO near3 (layer film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:57
13	46920	control near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:55
14	2460	((silicon near oxide/silicon near nitride/silicon near oxide) (ONO near3 (layer film))) and (control near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 11:19
16	2387	(control near gate) with (sidewall\$1 (side near wall\$1) spacer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:57
17	707	((silicon near oxide/silicon near nitride/silicon near oxide) (ONO near3 (layer film))) and ((control near gate) with (sidewall\$1 (side near wall\$1) spacer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:56
19	627	((silicon near oxide/silicon near nitride/silicon near oxide) ONO) with (sidewall\$1 (side near wall\$1) spacer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:57
21	246	((control near gate) with (sidewall\$1 (side near wall\$1) spacer\$1)) and (((silicon near oxide/silicon near nitride/silicon near oxide) ONO) with (sidewall\$1 (side near wall\$1) spacer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/09 14:58